

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSIII)

2SK2610

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

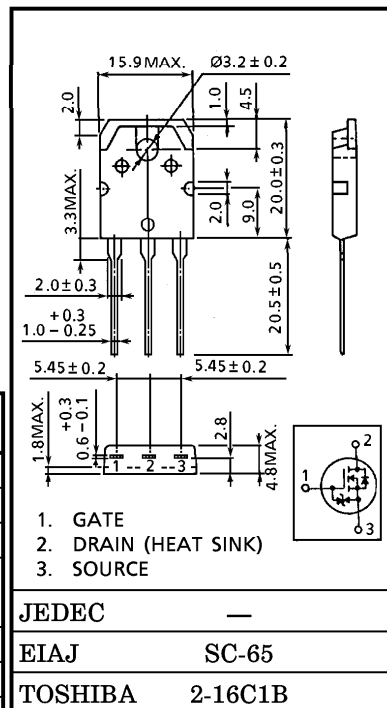
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 2.3 \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.4 S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu A$ (Max.) ($V_{DS} = 720 V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0 V$
($V_{DS} = 10 V, I_D = 1 mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Drain-Gate Voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	900	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	DC	I_D	5	A
	Pulse	I_{DP}	15	
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	150	W
Single Pulse Avalanche Energy**		E_{AS}	595	mJ
Avalanche Current		I_{AR}	5	A
Repetitive Avalanche Energy*		E_{AR}	15	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$



Weight : 4.6 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.833	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ C / W$

Note ;

- * Repetitive rating ; Pulse Width Limited by Max. junction temperature.
- ** $V_{DD} = 90 V, T_{ch} = 25^\circ C$ (initial), $L = 43.6 mH, I_{AR} = 5 A, R_G = 25 \Omega$

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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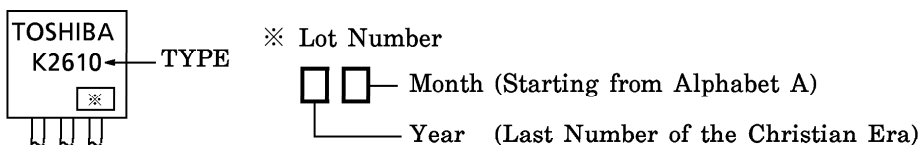
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

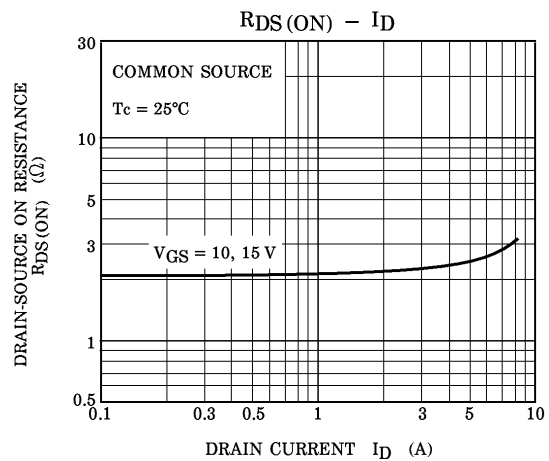
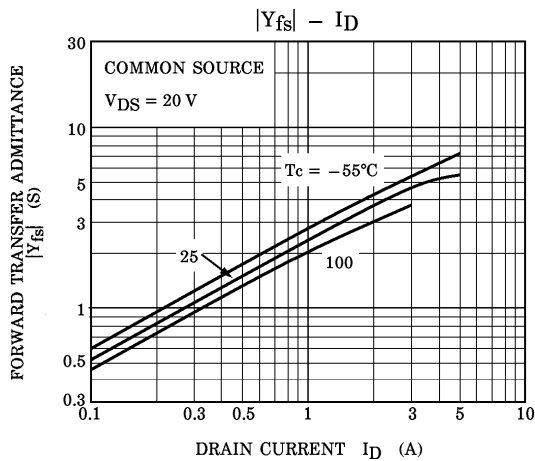
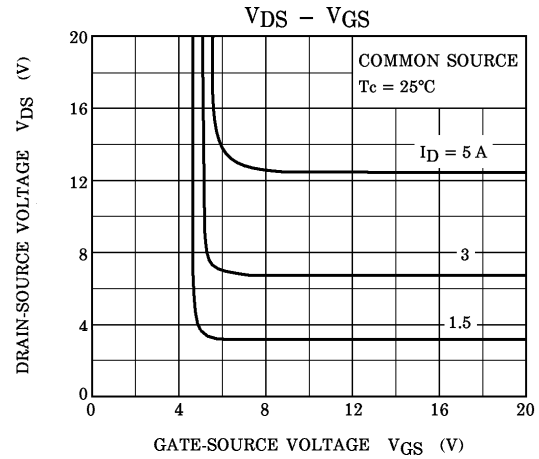
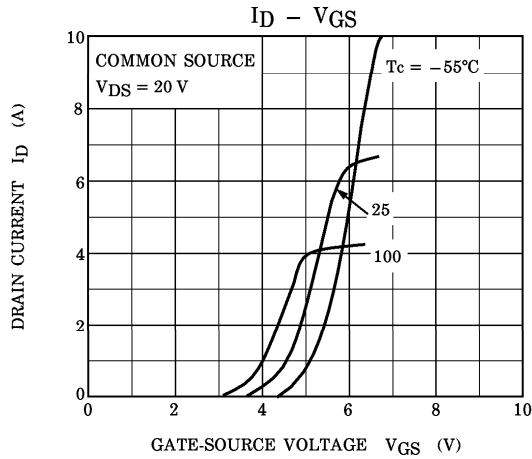
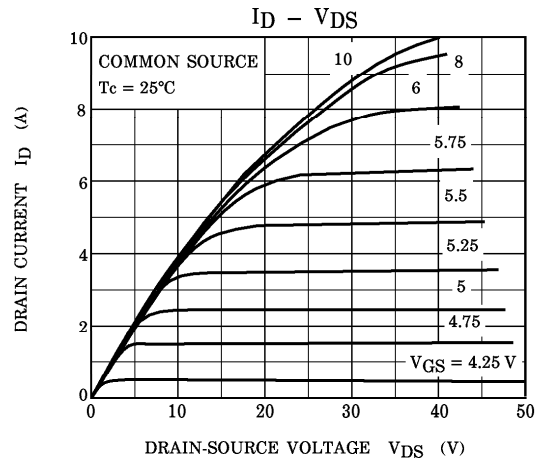
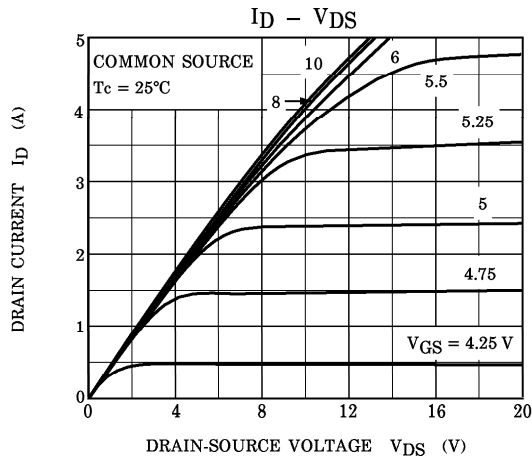
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA	
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 10\ \mu\text{A}, V_{DS} = 0\text{ V}$	± 30	—	—	V	
Drain Cut-off Current	I_{DSS}	$V_{DS} = 720\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	900	—	—	V	
Gate Threshold Voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V	
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}$	—	2.3	2.5	Ω	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 20\text{ V}, I_D = 3.0\text{ A}$	1.1	4.4	—	S	
Input Capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	—	1200	—	pF	
Reverse Transfer Capacitance	C_{rss}		—	20	—		
Output Capacitance	C_{oss}		—	120	—		
Switching Time	Rise Time	t_r		—	40	—	ns
	Turn-on Time	t_{on}		—	90	—	
	Fall Time	t_f		—	60	—	
	Turn-off Time	t_{off}		$V_{IN} : t_r, t_f < 5\text{ ns},$ $\text{Duty} \leq 1\%, t_w = 10\ \mu\text{s}$	—	200	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{DD} \cong 400\text{ V}, V_{GS} = 10\text{ V},$ $I_D = 5\text{ A}$	—	45	—	nC	
Gate-Source Charge	Q_{gs}		—	25	—		
Gate-Drain (“Miller”) Charge	Q_{gd}		—	20	—		

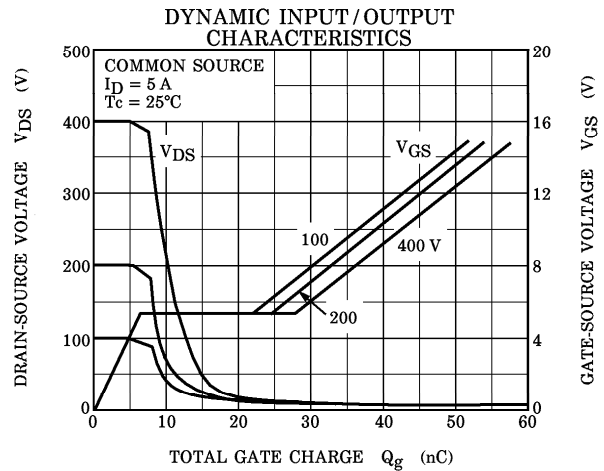
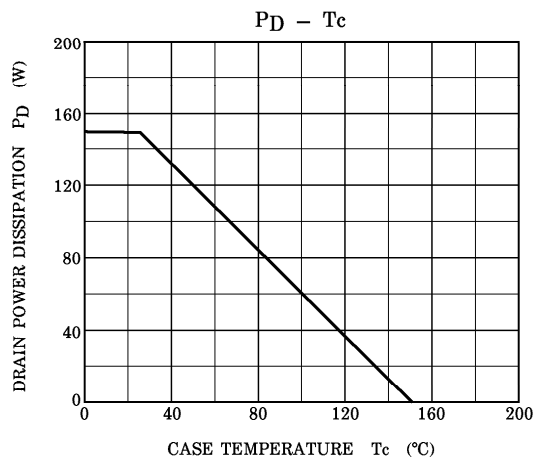
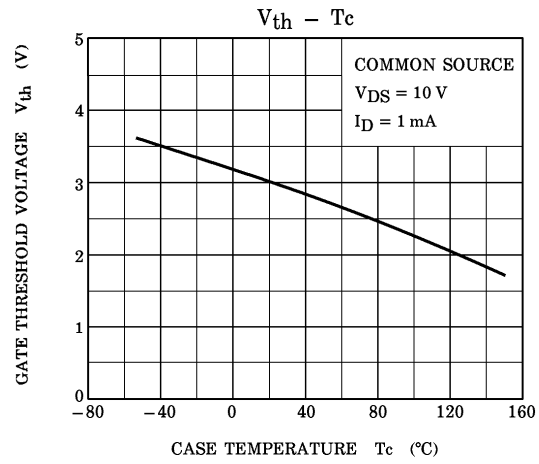
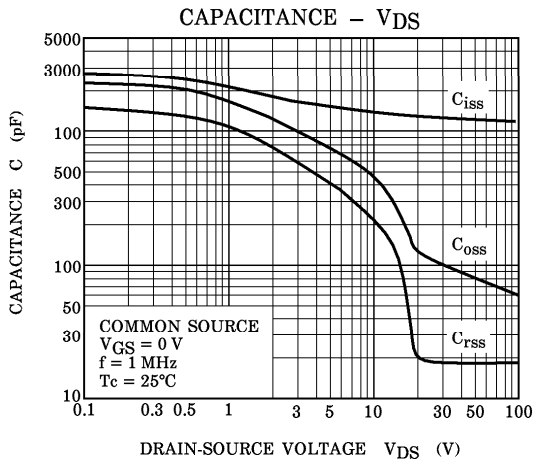
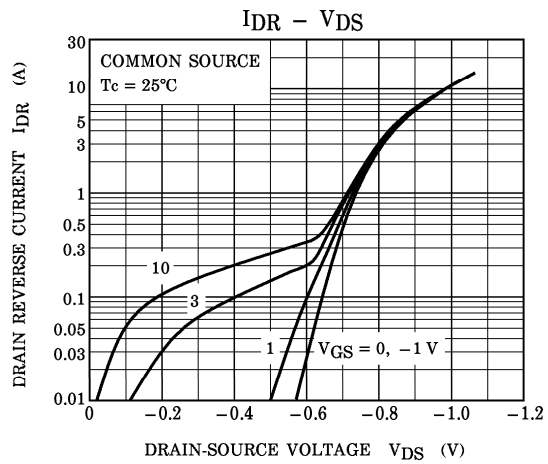
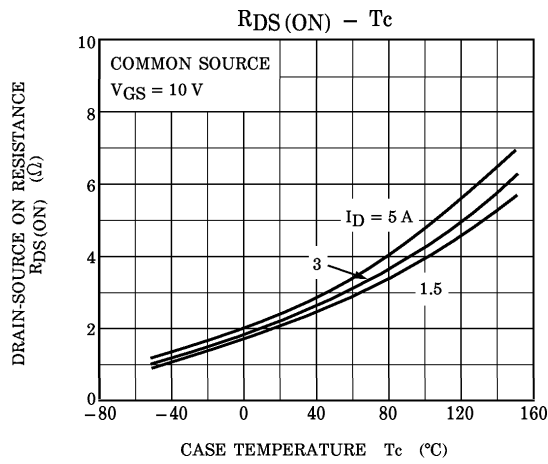
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

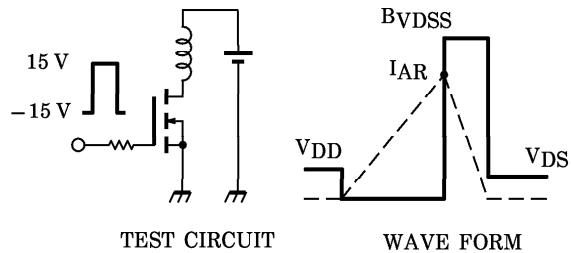
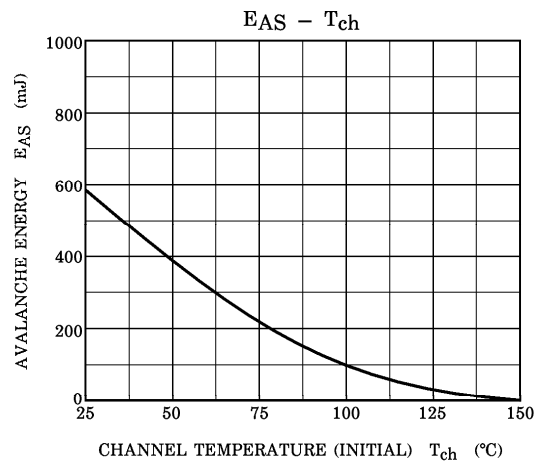
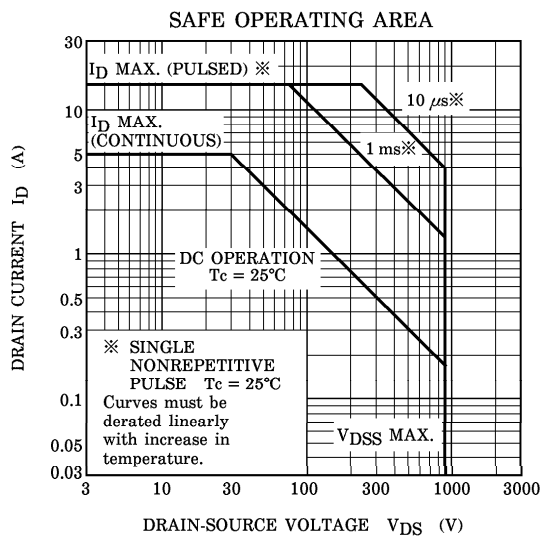
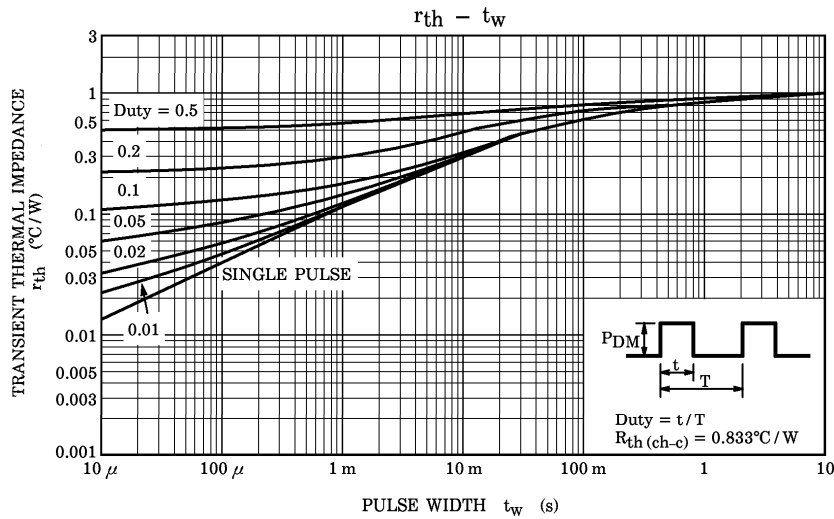
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	15	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.9	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$	—	1300	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	11	—	μC

MARKING









Peak $I_{AR} = 5 \text{ A}$, $R_G = 25 \Omega$
 $V_{DD} = 90 \text{ V}$, $L = 43.6 \text{ mH}$ $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BV_{DSS}}{BV_{DSS} - V_{DD}} \right)$